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(54) DYNAMIC RANDOM ACCESS MEMORY AND FORMING METHOD THEREFOR

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(57)ABSTRACT

A dynamic random access memory and a forming method therefor. The dynamic random access memory comprises: a substrate (100), which has opposite first surface (101) and second surface (102), and comprises several active regions (103), and each active region (103) comprises an isolation region (104), a channel region (105) and a word line region (106); a first isolation layer (108), which is located in the isolation region (104); a word line gate structure (111), which is located in the word line region (106); a first source/drain dope region (112), which is located in the channel region (105) on the first surface (101); a bit line layer (114) which is located on the first surface (101); a second source/drain dope region (116) which is located in the channel region (105) on the second surface (102); and several capacitor structures (119), which are located on the second surface (102).

